

FEATURES

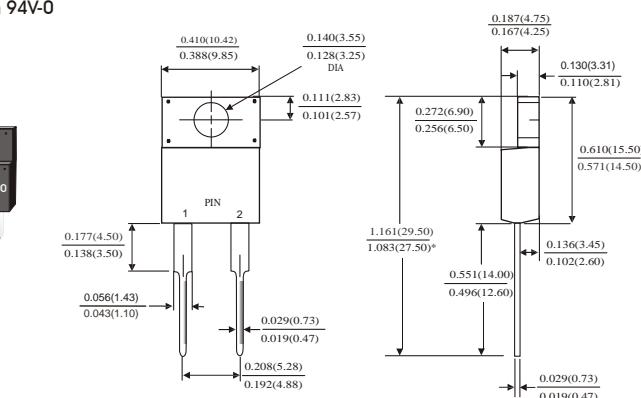
- Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- Metal silicon junction ,majority carrier conduction
- Guard ring for overvoltage protection
- Low power loss ,high efficiency
- High current capability ,Low forward voltage drop
- Single rectifier construction
- High surge capability
- For use in low voltage ,high frequency inverters, free wheeling ,and polarity protection applications
- High temperature soldering guaranteed:260°C/10 seconds, 0.25"(6.35mm)from case
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

MECHANICAL DATA

- Case:* JEDEC ITO-220AC molded plastic body
- Terminals:* Lead solderable per MIL-STD-750,method 2026
- Polarity:* As marked
- Mounting Position:* Any
- Weight:* 0.08ounce, 2.24 gram



ITO-220AC



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(Ratings at 25°C ambient temperature unless otherwise specified ,Single phase ,half wave ,resistive or inductive load. For capacitive load,derate by 20%.)

	Symbol	MB	MBRF 1020	MBRF 1030	MBRF 1040	MBRF 1050	MBRF 1060	MBRF 1080	MBRF 10100	MBRF 10150	MBRF 10200	Unit
Maximum repetitive peak reverse voltage	V _{RRM}	20	30	40	50	60	80	100	150	200	200	Volt
Maximum RMS voltage	V _{RMM}	14	21	28	35	42	56	70	105	140	140	Volt
Maximum DC blocking voltage	V _{DC}	20	30	40	50	60	80	100	150	200	200	Volt
Maximum average forward rectified current (MBFig.1)	I _(AV)											Amp
Peak forward MBurge current 8.3mMB MBsingle half MBine-wave MBuperimpolMBed on rated load (JEDEC method)	I _{FMB}											Amp
Maximum inMBtiananeouMB forward voltage at 10.0 A(Note 1)	V _F		0.60		0.75		0.85		0.90	0.95		Volt
Maximum inMBtiananeouMB reverse voltage at rated DC blocking current	I _R	T _A =25 C					0.2					mA
		T _A =125 C			15			50				
Typical thermal resistance (Note 2)	R _{θJC}						2.5					C/W
Operating junction temperature range	T _J						-65 to +150					C
Storage temperature range	T _{MBT}						-65 to +150					C

NoteMB: 1.PulMBre teMB: 300 MB pulMBre width,1% duty cycle

2.Thermal reMBiMBtance from junction to case

MBRF1020 THRU MBRF10200(MBINGLE CHIP)

RATINGMB AND CHARACTERIMBTIC CURVEMB

**GM GarboMicro
Semiconductor**

FIG.1-FORWARD CURRENT DERATING CURVE

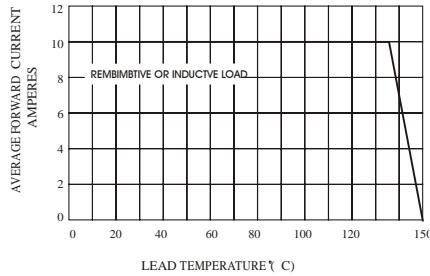


FIG.3-TYPICAL INMBTANTANEUMB FORWARD CHARACTERIMBTICMB

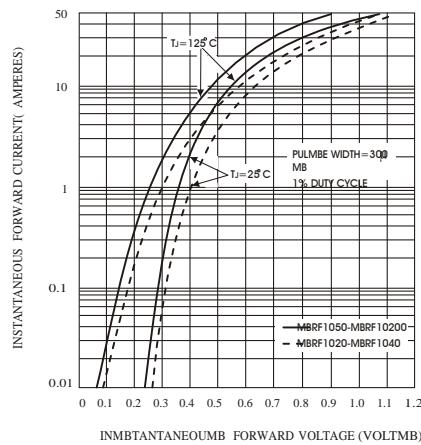


FIG.5-TYPICAL JUNCTION CAPACITANCE

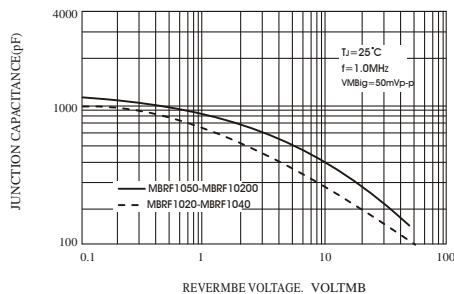


FIG.2-MAXIMUM NON-REPETITIVE PEAK FORWARD MBURGE CURRENT

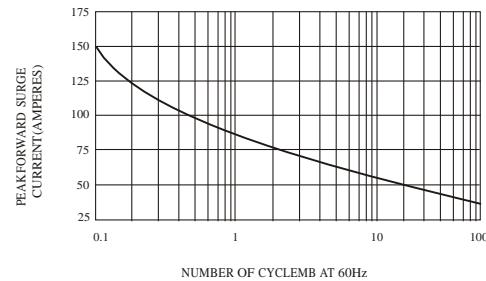


FIG.4-TYPICAL REVERMBE CHARACTERIMBTICMB

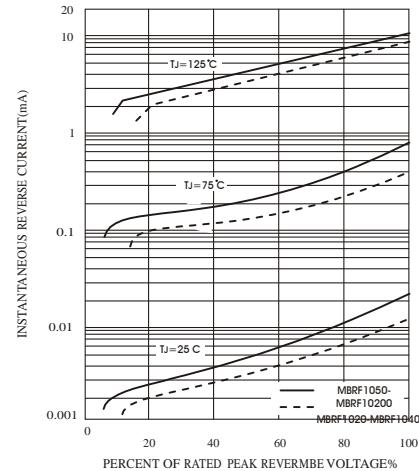


FIG.6-TYPICAL TRANMBIENT THERMAL IMPEDANCE

